

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
80V	7mΩ @ V <sub>GS</sub> = 10V	68A
	10.5mΩ @ V <sub>GS</sub> = 6V	56A

## Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

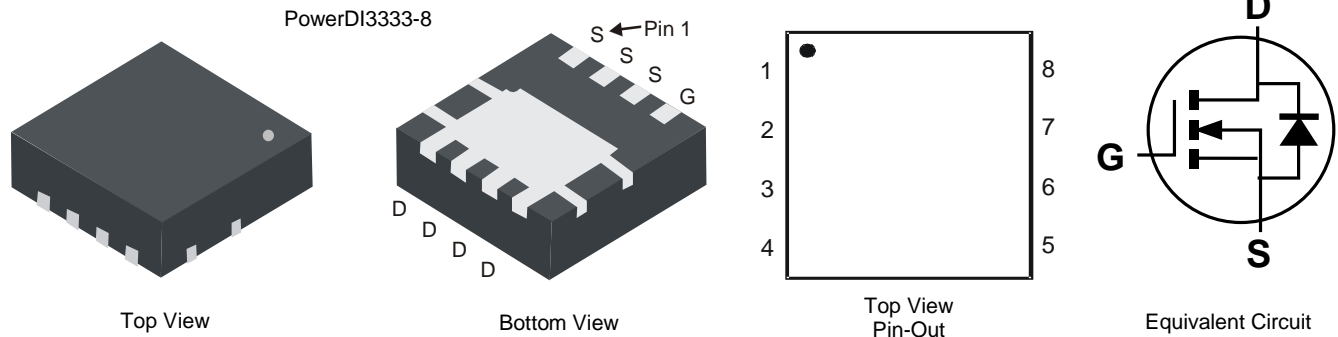
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- Low R<sub>DS(ON)</sub> – Ensures On-State Losses are Minimized
- Excellent Q<sub>gd</sub> × R<sub>DS(ON)</sub> Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMTH8008SFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (Approximate)

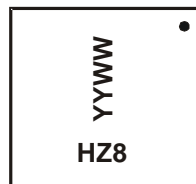


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH8008SFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMTH8008SFGQ-13	PowerDI3333-8	3,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



HZ8 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 20 = 2020)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	80	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	68
		T <sub>C</sub> = +100°C	48
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>A</sub> = +25°C	17
		T <sub>A</sub> = +100°C	12
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	68	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	272	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	272	A
Avalanche Current, L = 1mH (Note 8)	I <sub>AS</sub>	18.7	A
Avalanche Energy, L = 1mH (Note 8)	E <sub>AS</sub>	174.85	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.2
Thermal Resistance, Junction to Ambient (Note 5)		Steady State	R <sub>θJA</sub>
Total Power Dissipation (Note 6)	P <sub>D</sub>	T <sub>A</sub> = +25°C	3.2
Thermal Resistance, Junction to Ambient (Note 6)		Steady State	R <sub>θJA</sub>
Total Power Dissipation (Note 7)	P <sub>D</sub>	T <sub>C</sub> = +25°C	50
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	3.0
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	5.0	7	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 14A
		—	7.1	10.5		V <sub>GS</sub> = 6V, I <sub>D</sub> = 12A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 14A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>ISS</sub>	—	1945	—	pF	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>OSS</sub>	—	750	—		
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	45.8	—		
Gate Resistance	R <sub>G</sub>	—	1.8	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 5V)	Q <sub>G</sub>	—	18.4	—	nC	V <sub>DS</sub> = 40V, I <sub>D</sub> = 14A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	31.7	—		
Gate-Source Charge	Q <sub>GS</sub>	—	8.3	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	8.6	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	9.2	—	ns	V <sub>DD</sub> = 40V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 14A, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>R</sub>	—	11.8	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	27.0	—		
Turn-Off Fall Time	t <sub>F</sub>	—	17.3	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	40.6	—	ns	I <sub>S</sub> = 14A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>R</sub>	—	50.9	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

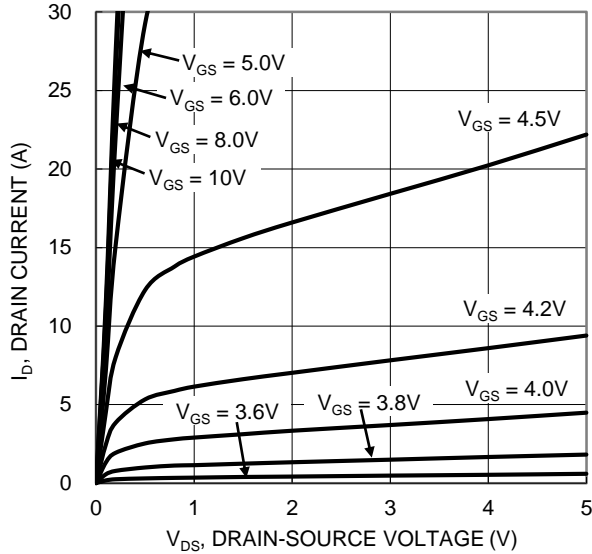


Figure 1. Typical Output Characteristic

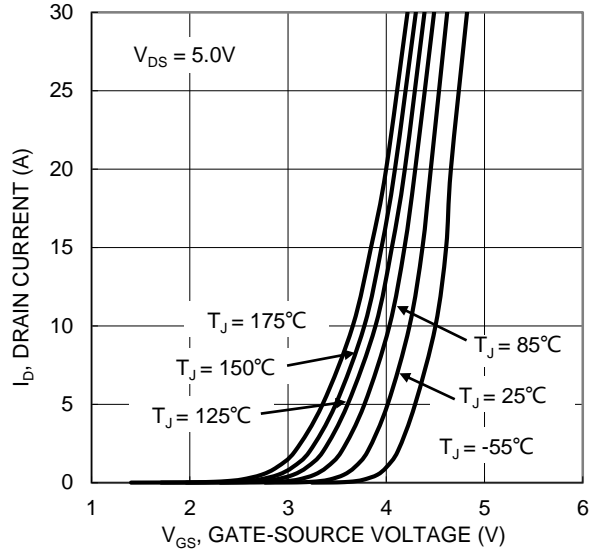


Figure 2. Typical Transfer Characteristic

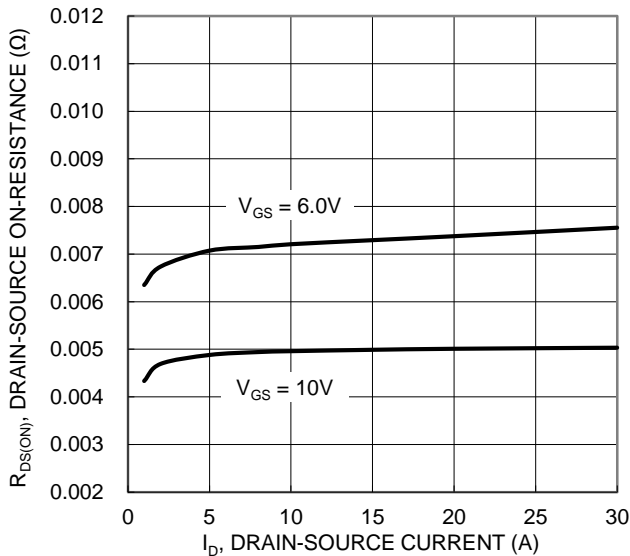


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

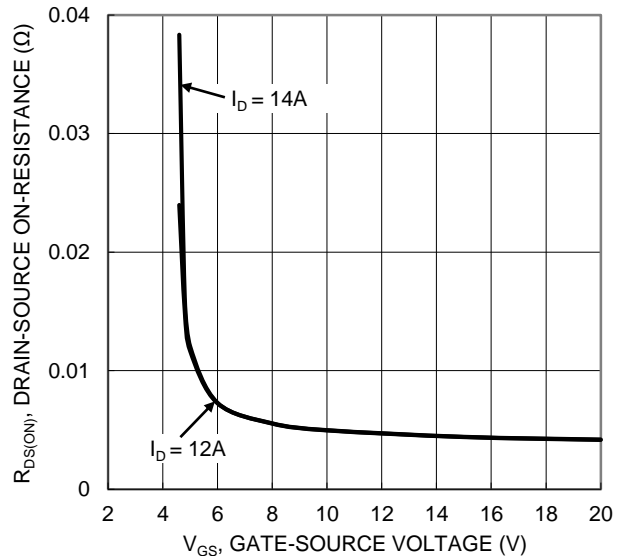


Figure 4. Typical Transfer Characteristic

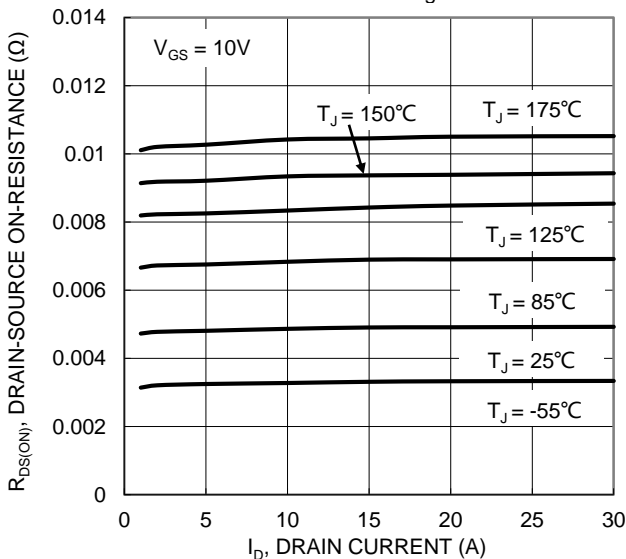


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

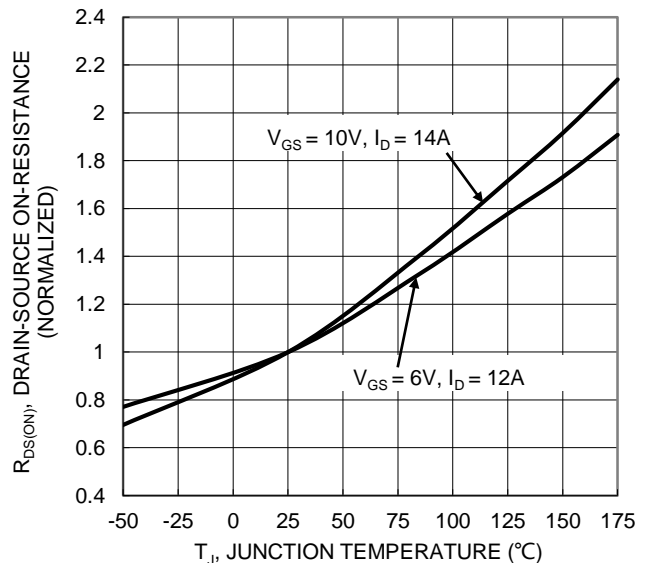


Figure 6. On-Resistance Variation with Temperature

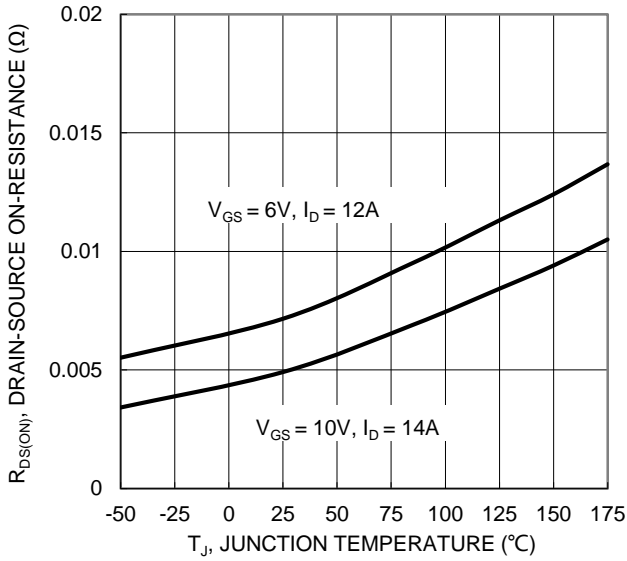


Figure 7. On-Resistance Variation with Temperature

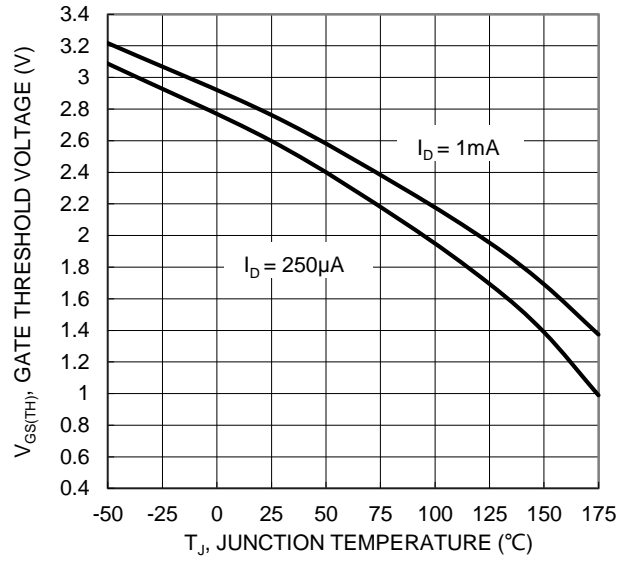


Figure 8. Gate Threshold Variation vs. Junction Temperature

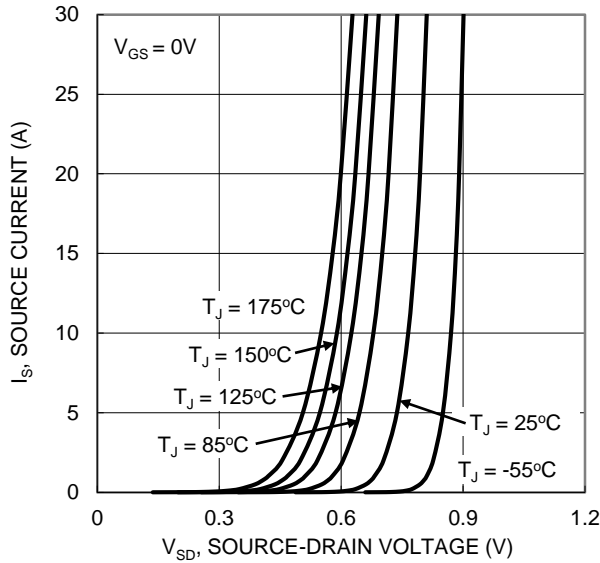


Figure 9. Diode Forward Voltage vs. Current

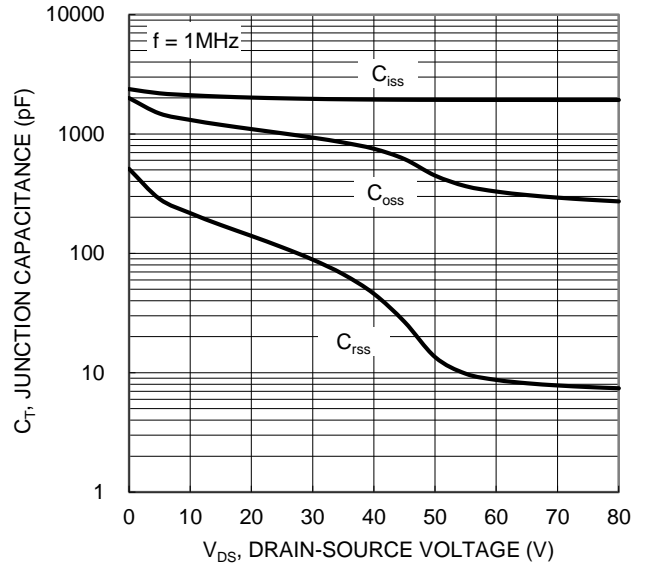


Figure 10. Typical Junction Capacitance

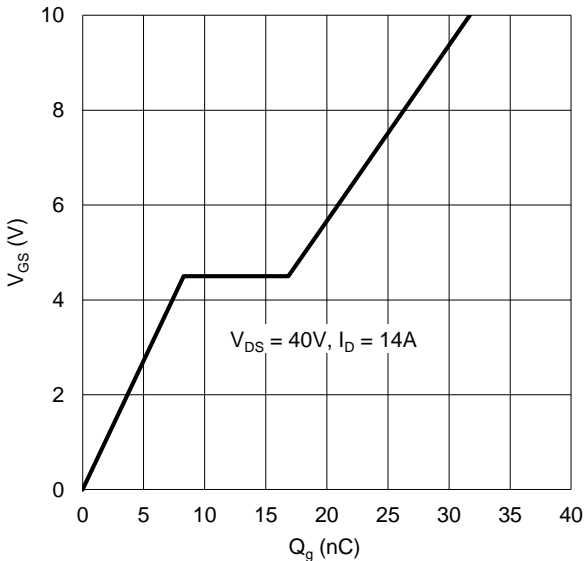


Figure 11. Gate Charge

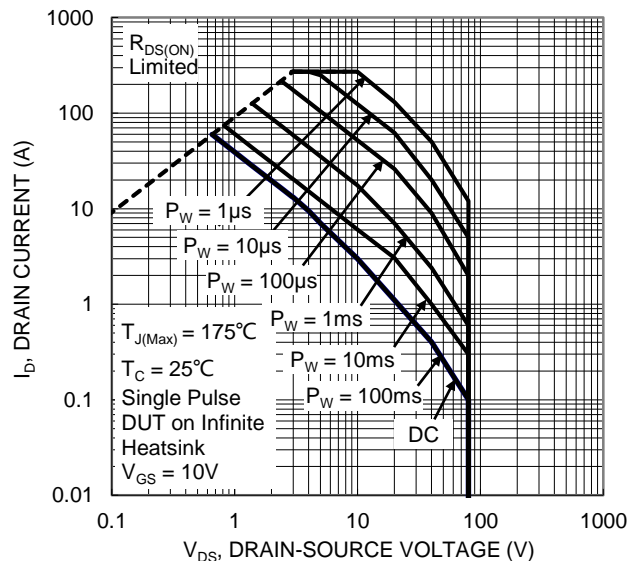


Figure 12. SOA, Safe Operation Area

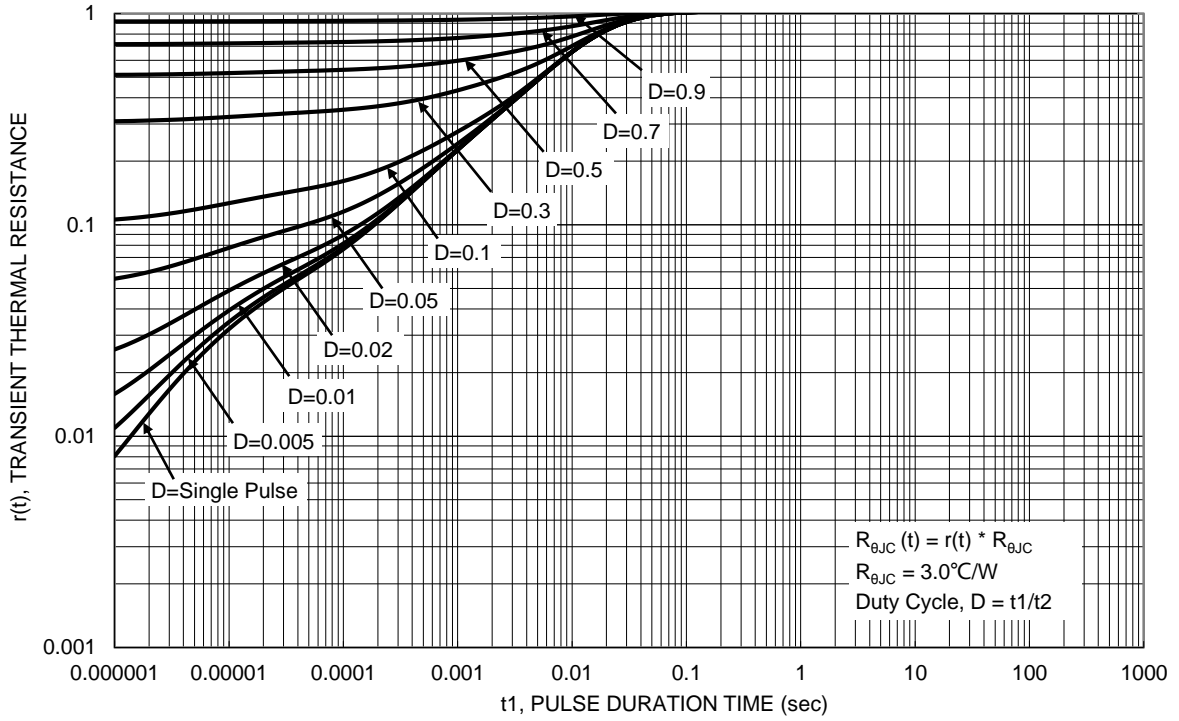
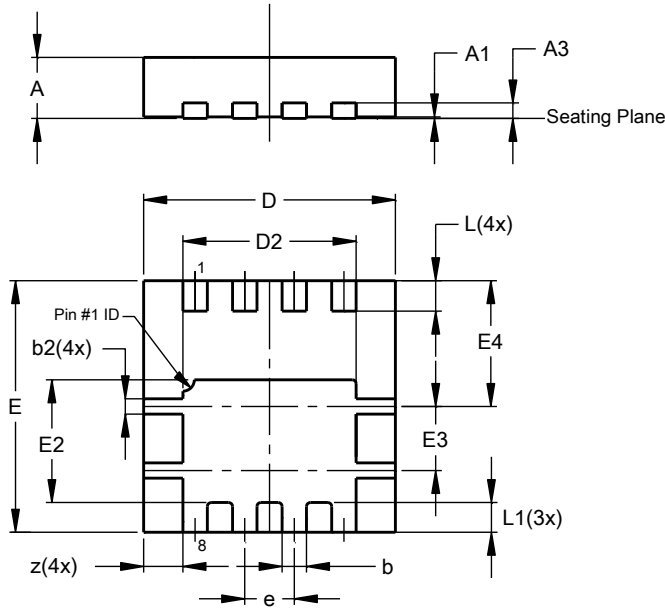


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**

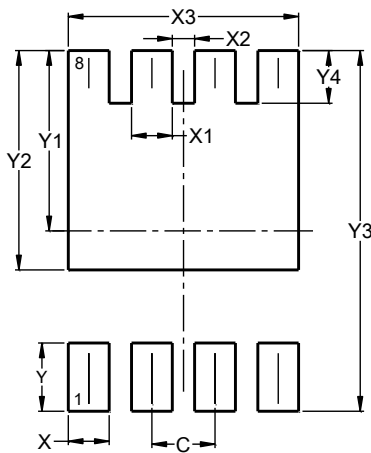


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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